

ABSTRACT

In one aspect, provided is an etching solution excellent in storage stability and capable of inhibiting etching and improving the quality of a surface of a layer being etched after etching. In one aspect, the present disclosure relates to an etching solution for etching a layer being etched containing at least one metal, the etching solution is obtainable by blending a nitrogen-containing compound having a ratio C/N of the number of carbon atoms (C) to the number of nitrogen atoms (N) in one molecule of 2.2 or more and an acid including an organic acid, nitric acid, and phosphoric acid, and water, in which a blending amount of the organic acid in the etching solution is 50% by mass or more.